

IRG4BC20MD-SPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH
ULTRAFAST SOFT RECOVERY DIODE

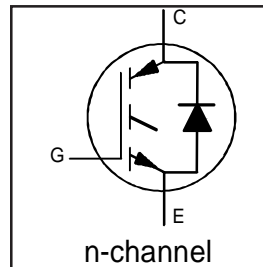
Short Circuit Rated
Fast IGBT

Features

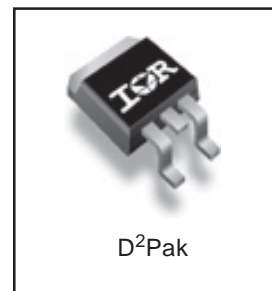
- Rugged: 10µsec short circuit capable at $V_{GS}=15V$
- Low $V_{CE(on)}$ for 4 to 10kHz applications
- IGBT Co-packaged with ultra-soft-recovery antiparallel diode
- Industry standard D²Pak package
- Lead-Free

Benefits

- Offers highest efficiency and short circuit capability for intermediate applications
- Provides best efficiency for the mid range frequency (4 to 10kHz)
- Optimized for Appliance Motor Drives, Industrial (Short Circuit Proof) Drives and Intermediate Frequency Range Drives
- High noise immune "Positive Only" gate drive- Negative bias gate drive not necessary
- For Low EMI designs- requires little or no snubbing
- Single Package switch for bridge circuit applications
- Compatible with high voltage Gate Driver IC's
- Allows simpler gate drive



$V_{CES} = 600V$
$V_{CE(on)} \text{ typ.} = 1.85V$
@ $V_{GE} = 15V, I_C = 11A$



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	18	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	11	
I_{CM}	Pulsed Collector Current ①	36	
I_{LM}	Clamped Inductive Load Current ②	36	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	7.0	
t_{sc}	Short Circuit Withstand Time	10	µs
I_{FM}	Diode Maximum Forward Current	36	A
V_{GE}	Gate-to-Emitter Voltage	± 20	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	60	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	24	
T_J	Operating Junction and	-55 to +150	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	-----	-----	2.1	°C/W
$R_{\theta JC}$	Junction-to-Case - Diode	-----	-----	2.5	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	-----	0.50	-----	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	-----	-----	80	
W_t	Weight	-----	2 (0.07)	-----	g (oz)

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage ^③	600	----	----	V	$V_{GE} = 0V, I_C = 250\mu A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	----	0.67	----	V/°C	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	----	1.85	2.1	V	$I_C = 11A$ $V_{GE} = 15V$ $I_C = 18A$ $V_{GE} = 15V$ $I_C = 11A, T_J = 150^\circ\text{C}$ See Fig. 2, 5
		----	2.46	----		
		----	2.07	----		
$V_{GE(th)}$	Gate Threshold Voltage	4.0	----	6.5		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	----	-11	----	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ^④	3.0	3.6	----	S	$V_{CE} = 100V, I_C = 11A$
I_{CES}	Zero Gate Voltage Collector Current	----	----	250	μA	$V_{GE} = 0V, V_{CE} = 600V$ $V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
		----	----	2500		
V_{FM}	Diode Forward Voltage Drop	----	1.4	1.7	V	$I_C = 8.0A$ $V_{GE} = 15V$ $I_C = 8.0A, T_J = 150^\circ\text{C}$ See Fig. 13
		----	1.3	1.6		
I_{GES}	Gate-to-Emitter Leakage Current	----	----	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	----	39	59	nC	$I_C = 11A$ $V_{CC} = 400V$ $V_{GE} = 15V$ See Fig. 8
Q_{ge}	Gate - Emitter Charge (turn-on)	----	5.3	8.0		
Q_{gc}	Gate - Collector Charge (turn-on)	----	20	30		
$t_{d(on)}$	Turn-On Delay Time	----	21	----	ns	$T_J = 25^\circ\text{C}$ $I_C = 11A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 50\Omega$ Energy losses include "tail" and diode reverse recovery.
t_r	Rise Time	----	37	----		
$t_{d(off)}$	Turn-Off Delay Time	----	463	690		
t_f	Fall Time	----	340	510		
E_{on}	Turn-On Switching Loss	----	0.41	----	mJ	See Fig. 9, 10, 11, 18
E_{off}	Turn-Off Switching Loss	----	2.03	----		
E_{ts}	Total Switching Loss	----	2.44	3.7		
$t_{d(on)}$	Turn-On Delay Time	----	19	----	ns	$T_J = 150^\circ\text{C}$, $V_{CC} = 480V$ See Fig. 9, 10, 11, 18 $I_C = 6.5A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 50\Omega$ Energy losses include "tail" and diode reverse recovery.
t_r	Rise Time	----	41	----		
$t_{d(off)}$	Turn-Off Delay Time	----	590	----		
t_f	Fall Time	----	600	----		
E_{ts}	Total Switching Loss	----	3.49	----	mJ	Measured 5mm from package
L_E	Internal Emitter Inductance	----	7.5	----	nH	
C_{ies}	Input Capacitance	----	460	----	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$ See Fig. 7
C_{oes}	Output Capacitance	----	54	----		
C_{res}	Reverse Transfer Capacitance	----	14	----		
t_{rr}	Diode Reverse Recovery Time	----	37	55	ns	$T_J = 25^\circ\text{C}$ See Fig. 14 $T_J = 125^\circ\text{C}$ 14
		----	55	90		
I_{rr}	Diode Peak Reverse Recovery Current	----	3.5	5.0	A	$T_J = 25^\circ\text{C}$ See Fig. 15 $T_J = 125^\circ\text{C}$ 15
		----	4.5	8.0		
Q_{rr}	Diode Reverse Recovery Charge	----	65	138	nC	$T_J = 25^\circ\text{C}$ See Fig. 16 $T_J = 125^\circ\text{C}$ 16
		----	124	360		
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During t_b	----	240	----	A/ μs	$T_J = 25^\circ\text{C}$ See Fig. 17 $T_J = 125^\circ\text{C}$ 17
		----	210	----		

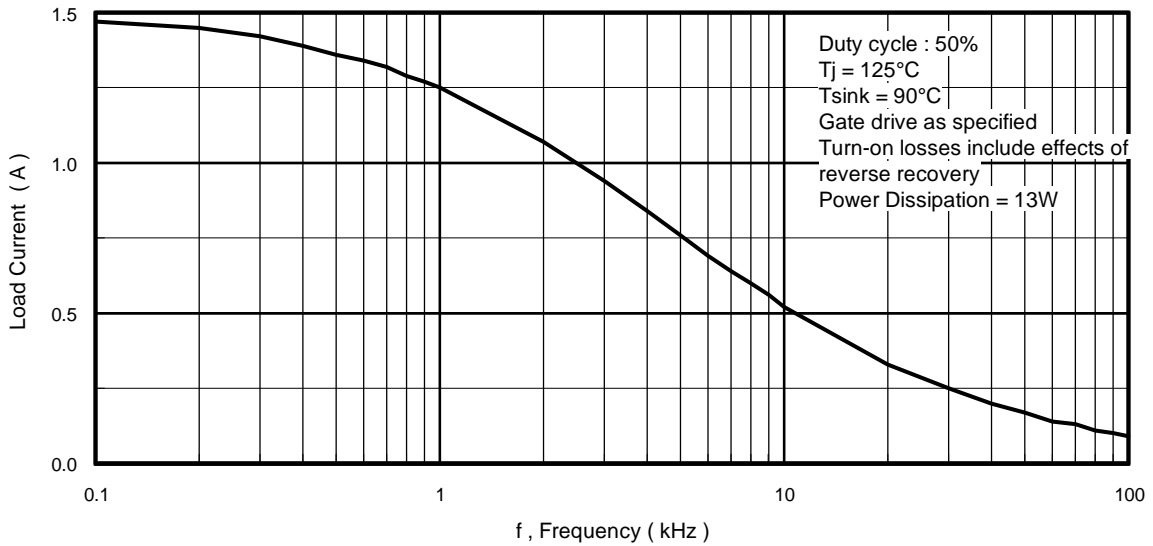


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

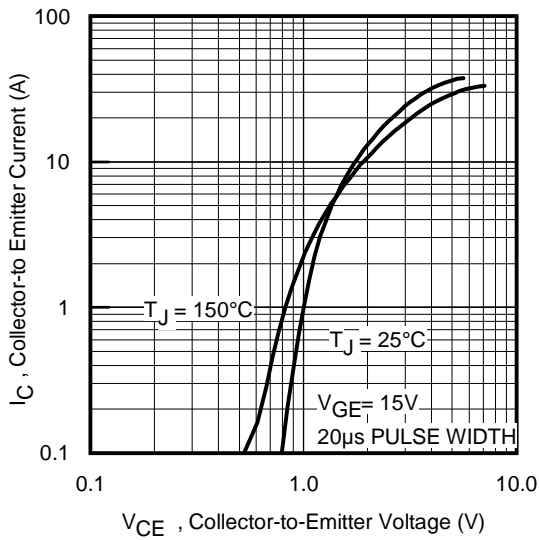


Fig. 2 - Typical Output Characteristics

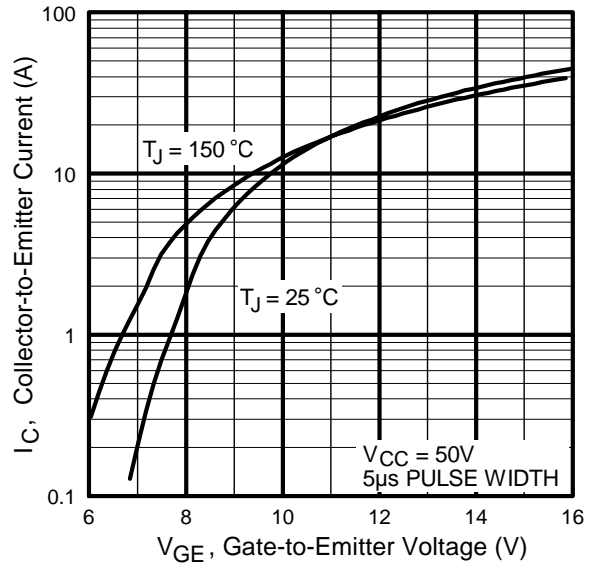


Fig. 3 - Typical Transfer Characteristics

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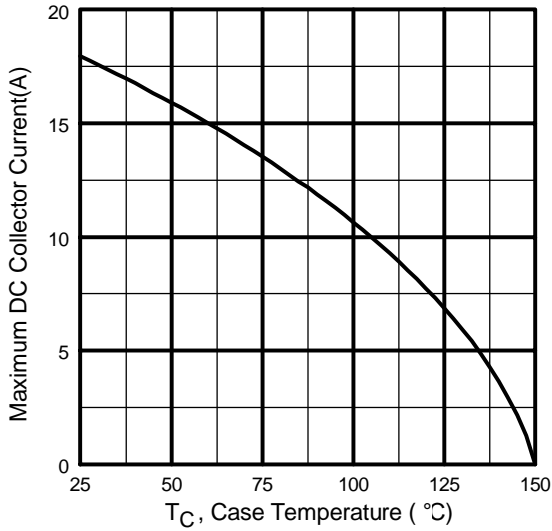


Fig. 4 - Maximum Collector Current vs. Case Temperature

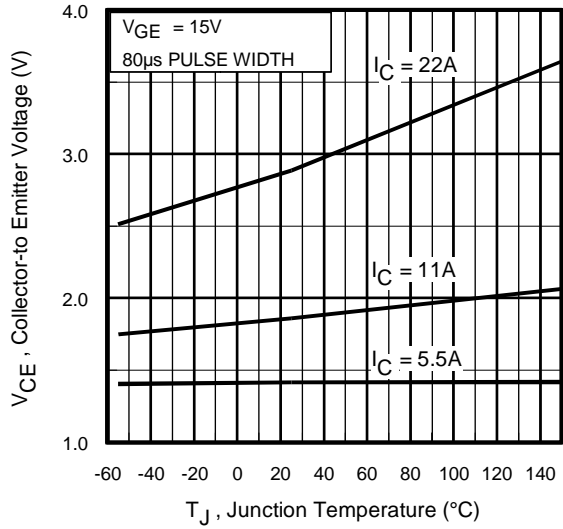


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

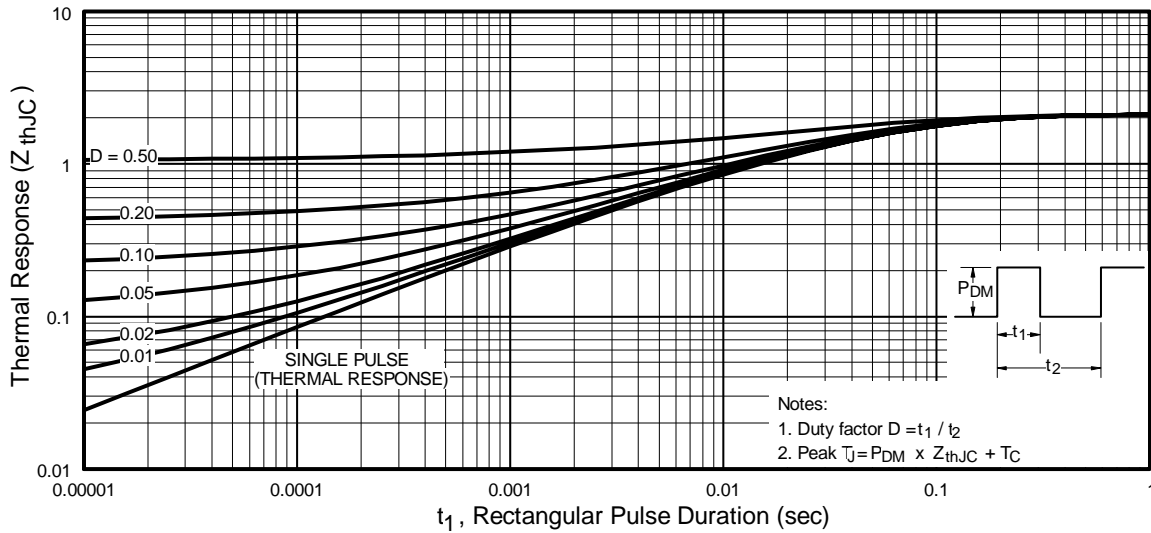


Fig. 6 - Maximum IGBT Effective Transient Thermal Impedance, Junction-to-Case

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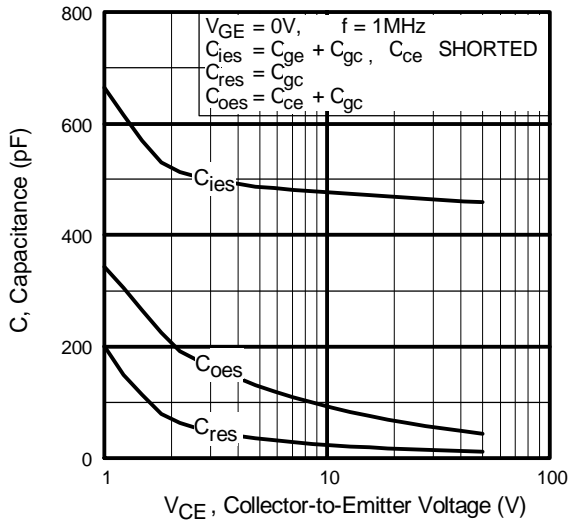


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

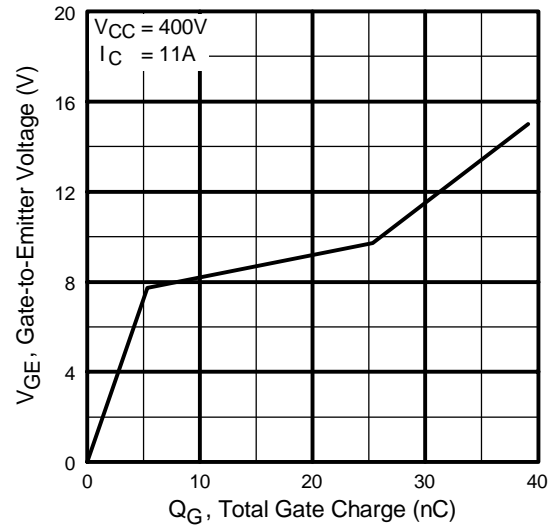


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

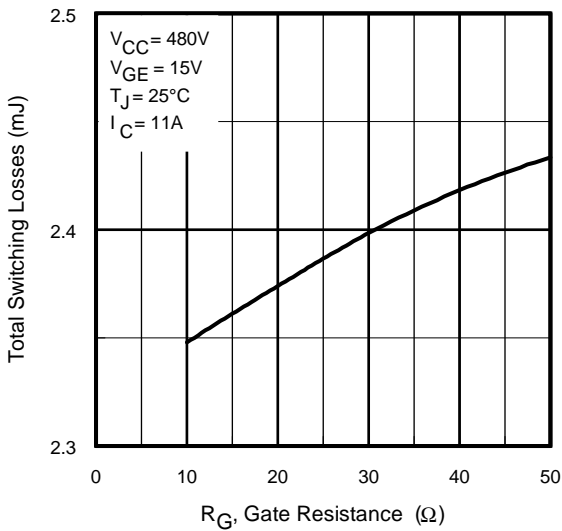


Fig. 9 - Typical Switching Losses vs. Gate Resistance

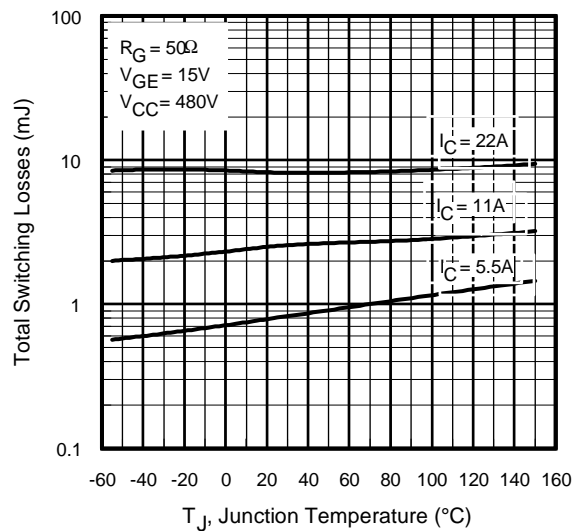


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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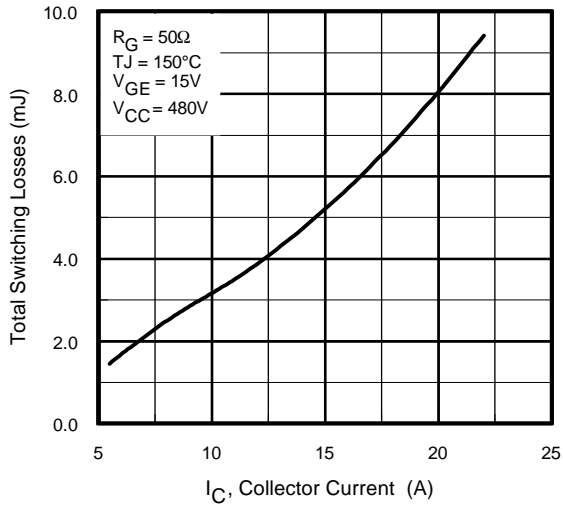


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

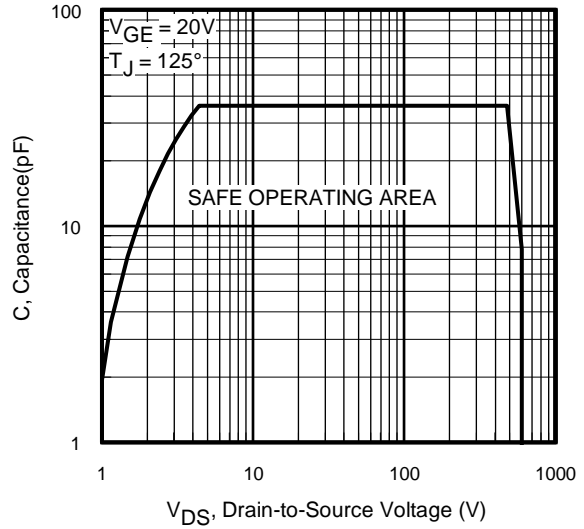


Fig. 12 - Turn-Off SOA

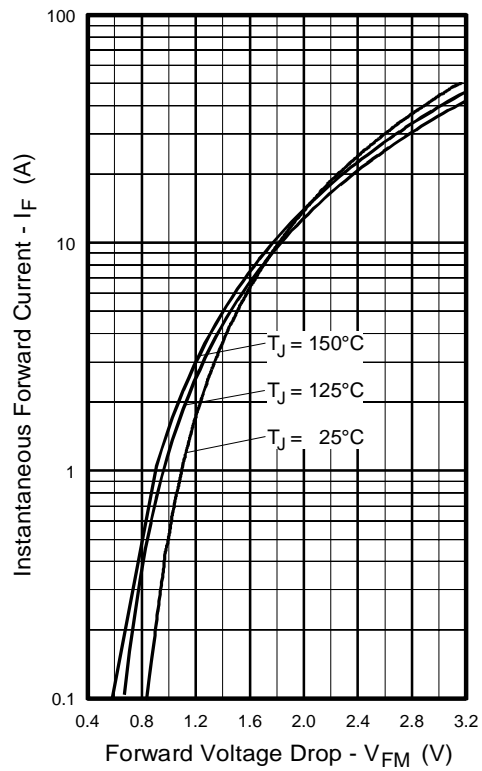


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

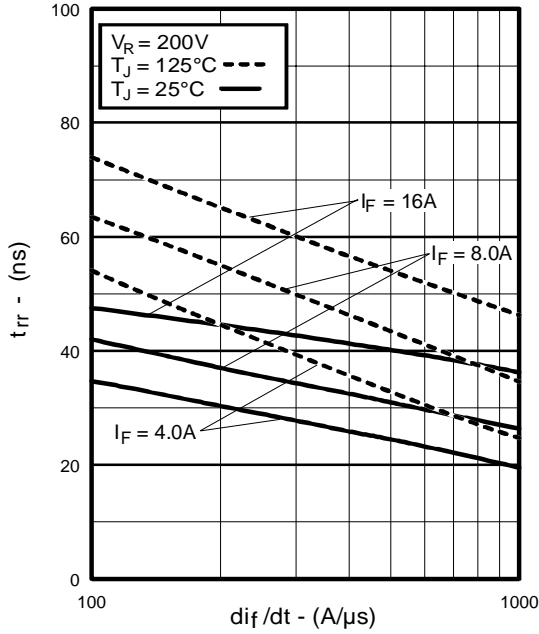


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

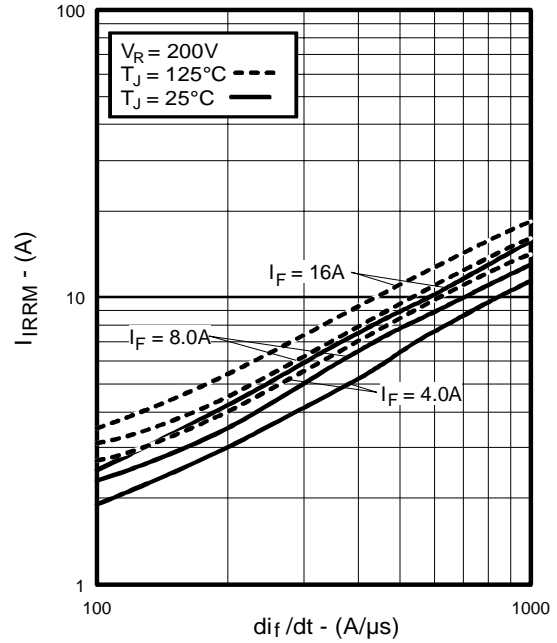


Fig. 15 - Typical Recovery Current vs. di_f/dt

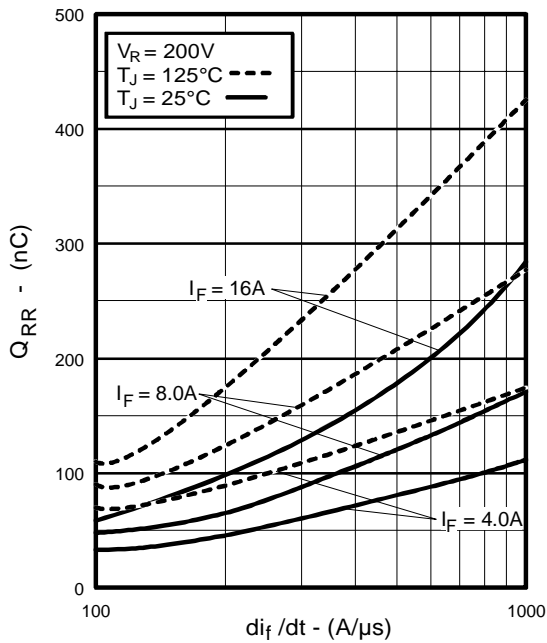


Fig. 16 - Typical Stored Charge vs. di_f/dt

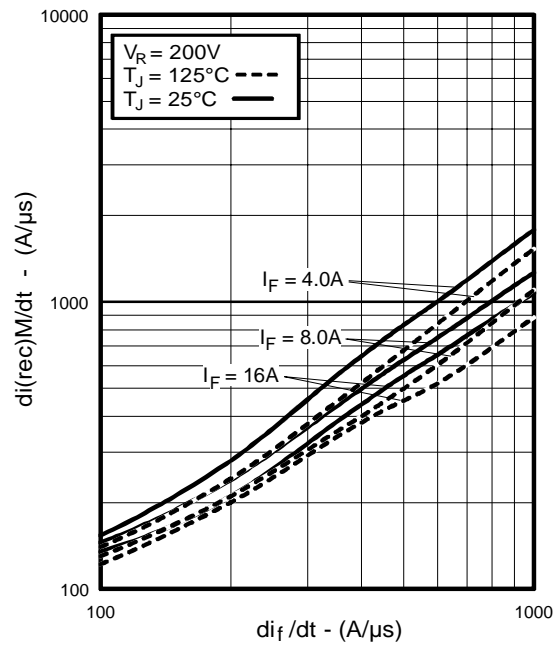


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

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International
IRF Rectifier

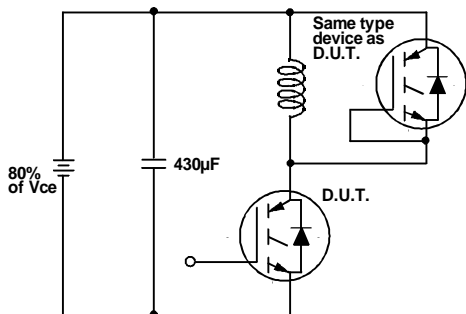


Fig. 18a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

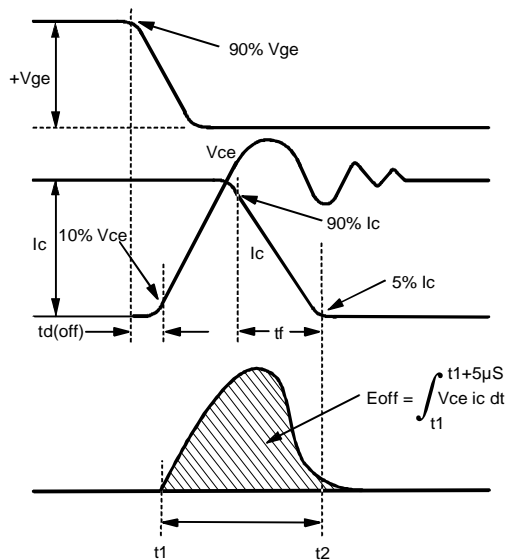


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

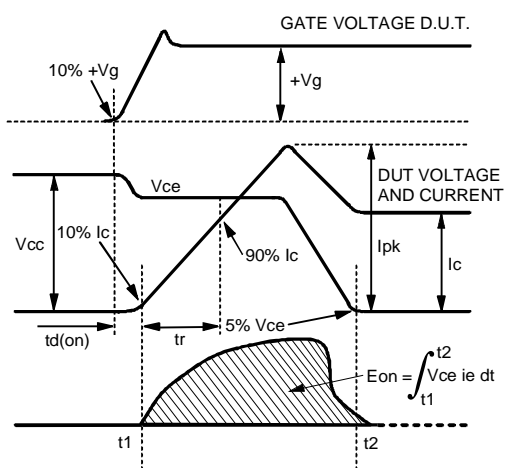


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

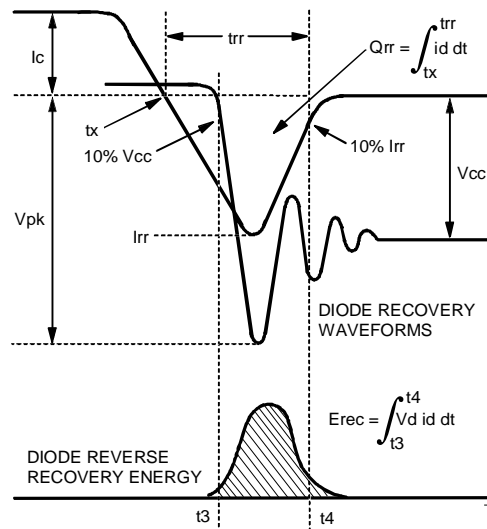


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{tr} , Q_{rr} , I_{rr}

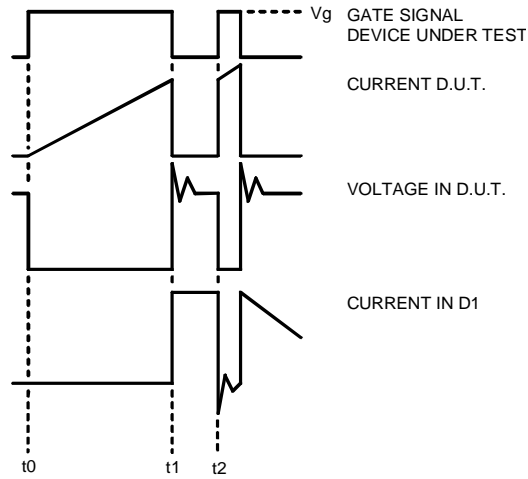


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

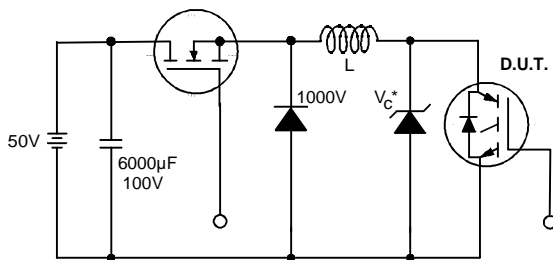


Figure 19. Clamped Inductive Load Test Circuit

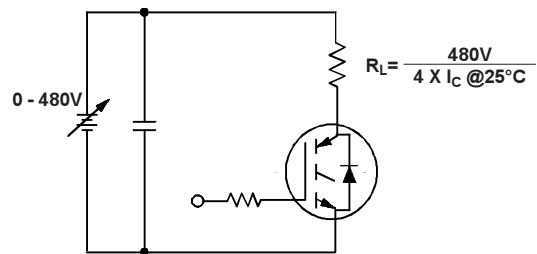


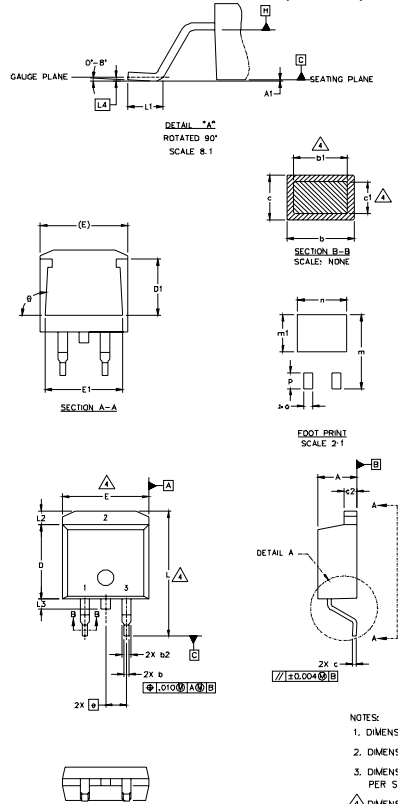
Figure 20. Pulsed Collector Current Test Circuit

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International
IR Rectifier

D²Pak Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1		0.127		.005	
b	0.51	0.99	.020	.039	4
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	
c	0.43	0.63	.017	.025	
c1	0.38	0.74	.015	.029	4
c2	1.14	1.40	.045	.055	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2		1.65		.065	
L3	1.27	1.78	.050	.070	
L4	0.25 BSC		.010 BSC		
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
θ	90°	9.3°	90°	9.3°	

LEAD ASSIGNMENTS

HEXFET	IGBTs CoPACK	DIODES
1.- GATE	1.- GATE	1.- ANODE *
2.- DRAIN	2.- COLLECTOR	2.- CATHODE
3.- SOURCE	3.- EMITTER	3.- ANODE

* PART DEPENDENT.

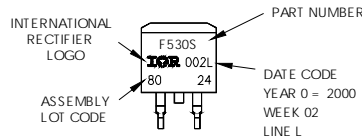
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

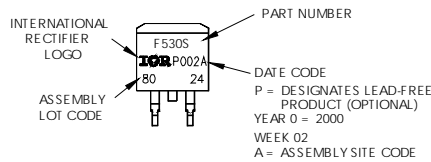
D²Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line
position indicates "Lead-Free"



OR

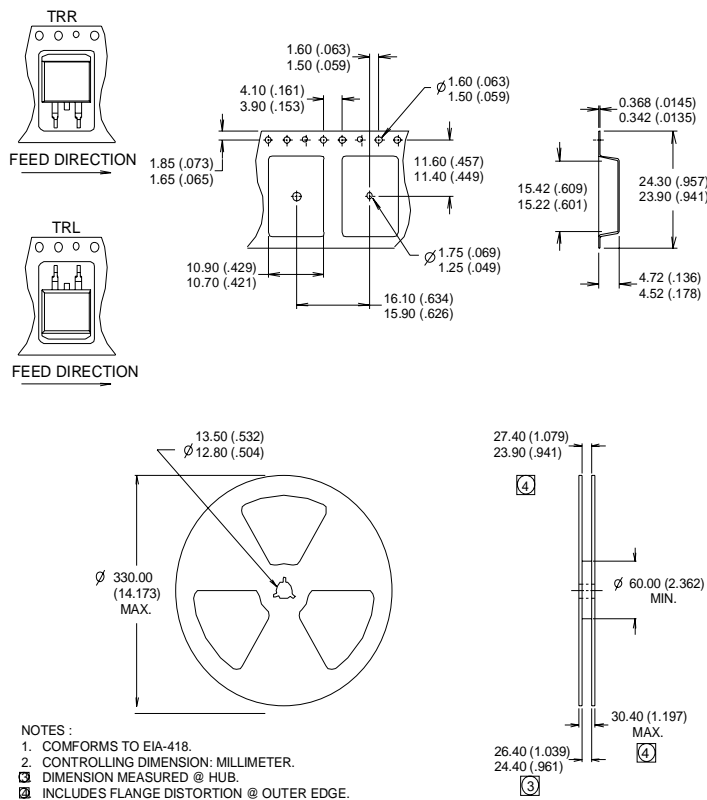


Notes:

- ① Repetitive rating: $V_{GE}=20V$; pulse width limited by maximum junction temperature (figure 20)
- ② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G = 50\Omega$ (figure 19)
- ③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ④ Pulse width $5.0\mu s$, single shot.

D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



Data and specifications subject to change without notice.
This product has been designed and qualified for the industrial market.
Qualification Standards can be found on IR's Web site.

International
IR Rectifier

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TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information. 07/04

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>